UMW FDV304P

P-Channel Enhancement MOSFET

1.Description

This P-Channel enhancement mode field effect transistors is produced using Fairchild's proprietary, high cell density, DMOStechnology. This very high density process is tailored to minimizeon-state resistance at low gate drive conditions.

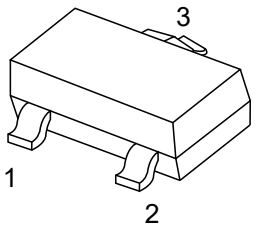
2.Features

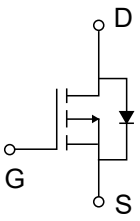
- $V_{DS\ (V)}$=-30V
- I_D=-4.2A(V_{GS}=-10V)
- $R_{DS(ON)}$<65mΩ(V_{GS}=-4.5V)
- $R_{DS(ON)}$<120mΩ(V_{GS}=-2.5V)

3.Pinning information

Pin	Symbol	Description
1	G	GATE
2	S	SOURCE
3	D	DRAIN

SOT-23





4.Absolute Maximum Ratings T_A= 25°C

Parameter		Symbol	Rating	Units
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	±12	
Continuous Drain Current	T_A=25°C	I_D	-4.2	A
	T_A=70°C		-3.5	
Pulsed Drain Current		I_{DM}	-30	
Power Dissipation	T_A=25°C	P_D	1.4	W
	T_A=70°C		1	
Thermal Resistance.Junction- to-Ambient t ≤ 10s		R_{thJA}	90	°C/W
Thermal Resistance.Junction- to-Ambient			125	
Thermal Resistance.Junction- to-Case		R_{thJC}	60	
Junction Temperature		T_J	150	°C
Junction and Storage Temperature Range		T_{STG}	-55 to 150	

5.Electrical Characteristics T_A= 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	V_{DSS}	I_D=250μA, V_{GS}=0V	-30			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-24V, V_{GS}=0V			-1	μA
		V_{DS}=-24V,V_{GS}=0V,T_J=55°C			-5	
Gate-Body leakage current	I_{GSS}	V_{DS}=0V, V_{GS}=±12V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=-250μA	-0.4		-1.3	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=-4.5V, I_D=-4A			65	mΩ
		V_{GS}=-2.5V, I_D=-1A			120	
On state drain current	$I_{D(ON)}$	V_{GS}=-4.5V, V_{DS}=-5V	-25			A
Forward Transconductance	g_{FS}	V_{DS}=-5V, I_D=-5A	7	11		S
Input Capacitance	C_{iss}	V_{GS}=0V, V_{DS}=-15V, f=1MHz		954		pF
Output Capacitance	C_{oss}			115		
Reverse Transfer Capacitance	C_{rss}			77		
Gate resistance	R_g	V_{GS}=0V, V_{DS}=0V, f=1MHz		6		Ω
Total Gate Charge	Q_g	V_{GS}=-4.5V, V_{DS}=-15V I_D=-4A		9.4		nC
Gate Source Charge	Q_{gs}			2		
Gate Drain Charge	Q_{gd}			3		
Turn-On DelayTime	$t_{D(on)}$	V_{GS}=-10V, V_{DS}=-15V R_L=3.6Ω, R_{GEN}=6Ω		6.3		ns
Turn-On Rise Time	t_r			3.2		
Turn-Off DelayTime	$t_{D(off)}$			38.3		
Turn-Off Fall Time	t_f			12		
Body Diode Reverse Recovery Time	t_{rr}	I_F=-4A, dI/dt=100A/μs		20.2		
Body Diode Reverse Recovery Charge	Q_{rr}	I_F=-5A, dI/dt=100A/μs		11.2		nC
Maximum Body-Diode Continuous Current	I_S				-2.2	A
Diode Forward Voltage	V_{SD}	I_S=-1A, V_{GS}=0V		-0.75	-1	V

6.1 Typical Characterisitics

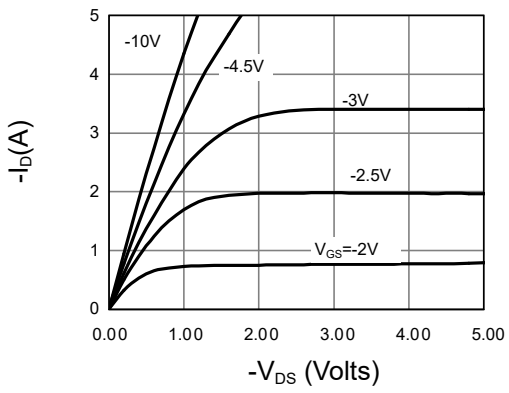


Fig 1: On-Region Characteristics

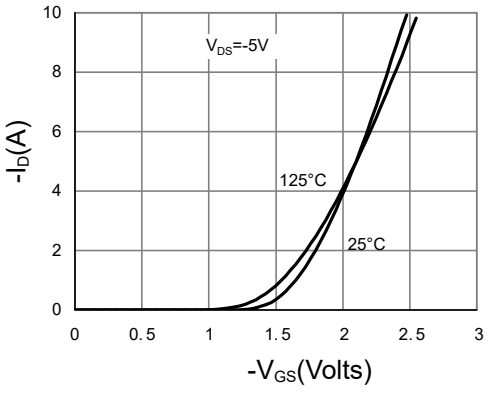


Figure 2: Transfer Characteristics

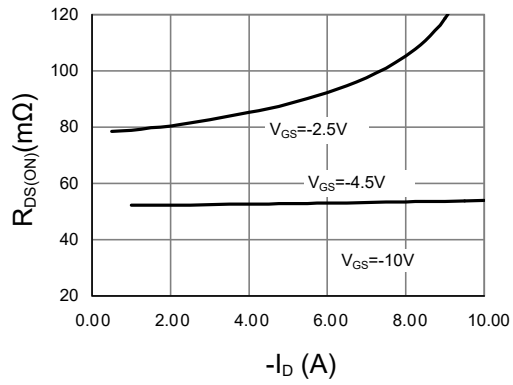


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

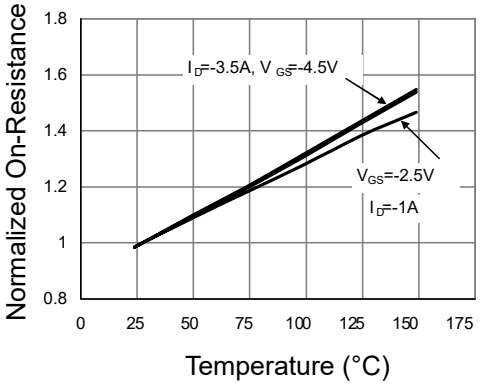


Figure 4: On-Resistance vs. Junction Temperature

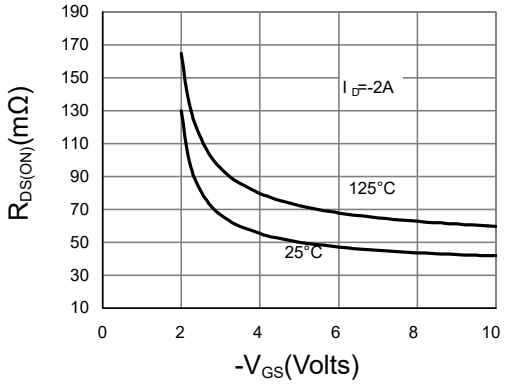


Figure 5: On-Resistance vs. Gate-Source Voltage

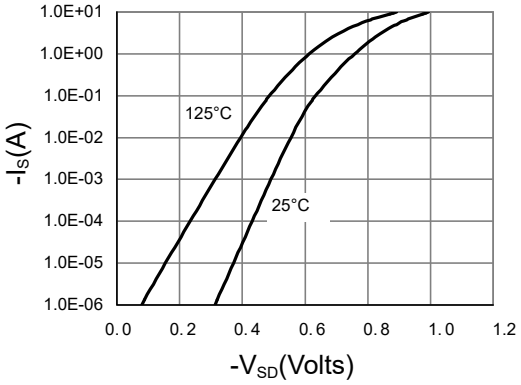


Figure 6: Body-Diode Characteristics

6.2 Typical Characterisitics

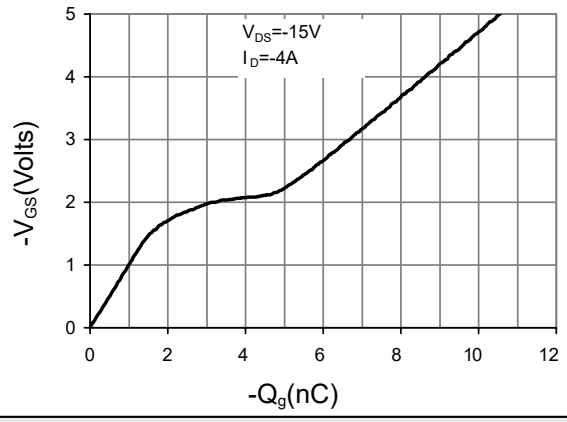


Figure 7: Gate-Charge Characteristics

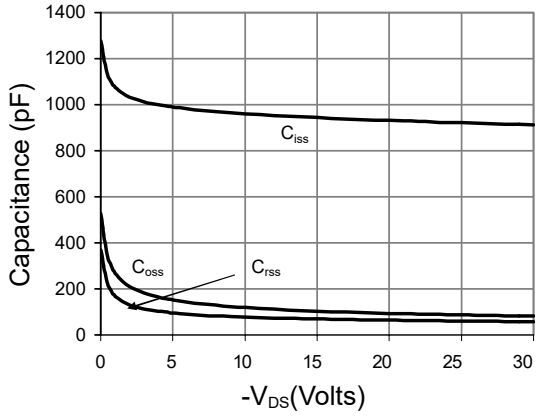


Figure 8: Capacitance Characteristics

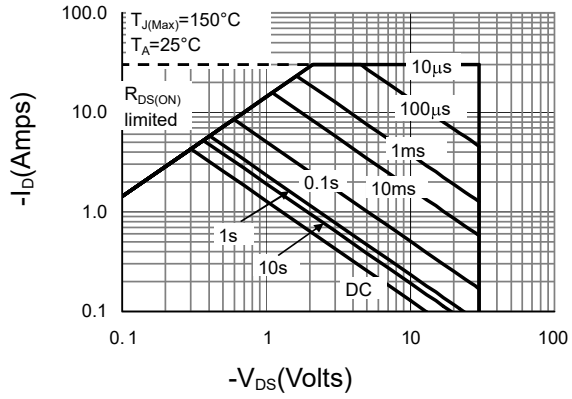


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

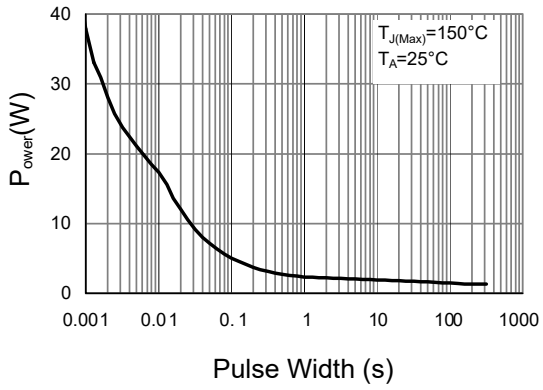


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

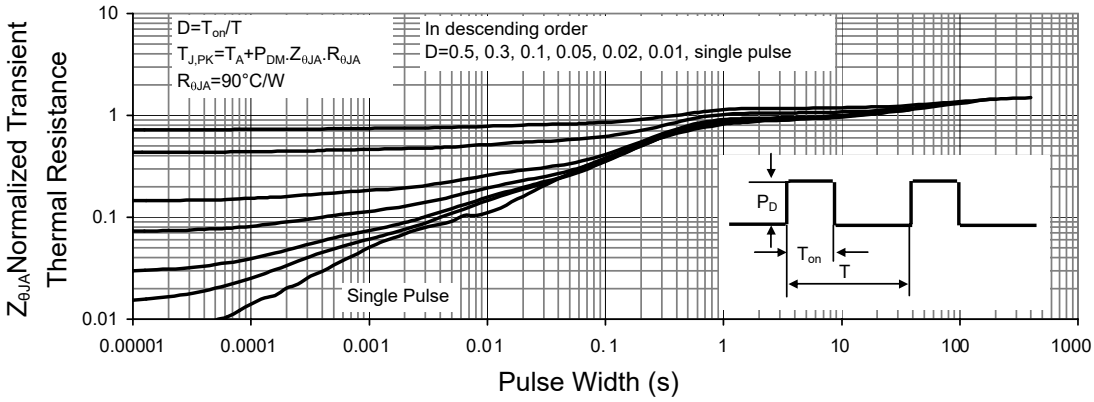
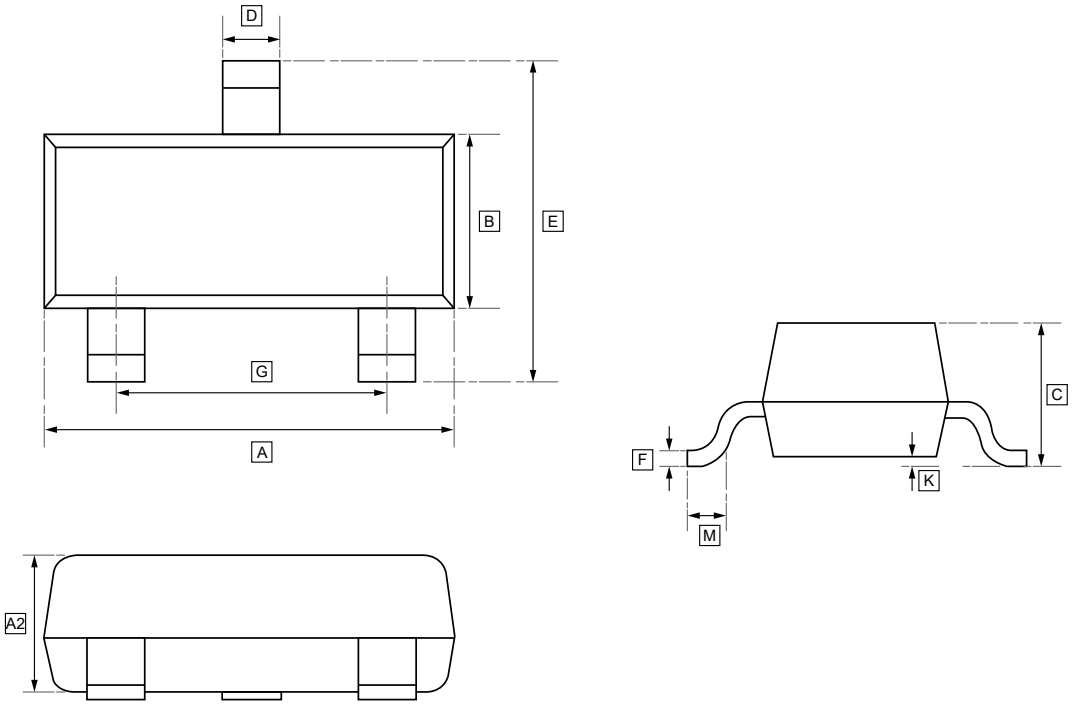


Figure 11: Normalized Maximum Transient Thermal Impedance

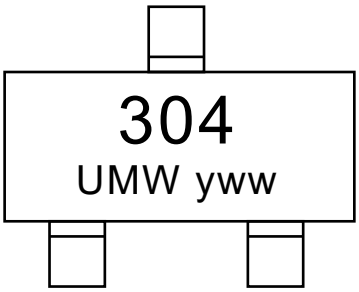
7.SOT-23 Package Outline Dimensions



DIMENSIONS (mm are the original dimensions)

Symbol	A	B	C	D	E	G	K	M	A2	F
Min	2.80	1.20	0.90	0.32	2.25	1.80	0.00	0.30	0.95	0.095
Max	3.04	1.40	1.10	0.55	2.55	2.00	0.10	-	1.05	0.115

8.Ordering Information



yww: Batch Code

Order Code	Package	Base QTY	Delivery Mode
UMW FDV304P	SOT-23	3000	Tape and reel

9.Disclaimer

UMW reserves the right to make changes to all products, specifications. Customers should obtain the latest version of product documentation and verify the completeness and currency of the information before placing an order.

When applying our products, please do not exceed the maximum rated values, as this may affect the reliability of the entire system. Under certain conditions, any semiconductor product may experience faults or failures. Buyers are responsible for adhering to safety standards and implementing safety measures during system design, prototyping, and manufacturing when using our products to prevent potential failure risks that could lead to personal injury or property damage.

Unless explicitly stated in writing, UMW products are not intended for use in medical, life-saving, or life-sustaining applications, nor for any other applications where product failure could result in personal injury or death. If customers use or sell the product for such applications without explicit authorization, they assume all associated risks.

When reselling, applying, or exporting, please comply with export control laws and regulations of China, the United States, the United Kingdom, the European Union, and other relevant countries, regions, and international organizations.

This document and any actions by UMW do not grant any intellectual property rights, whether express or implied, by estoppel or otherwise. The product names and marks mentioned herein may be trademarks of their respective owners.